

ABSTRACT OF THE DISCLOSURE

A semiconductor memory device that can be reduced in chip area while preventing degradation in characteristic is obtained. In DRAM, a plurality of memory cell array regions are arranged in matrix, spaced apart from each other in a row direction and in a column direction, on a semiconductor substrate. A sense amplifier region is arranged in a gap between the memory cell array regions in the column direction. An element forming a sense amplifier is arranged in the sense amplifier region. A subdecoder region is arranged in a gap between the memory cell array regions in the row direction. A cross region is arranged at an intersection of the sense amplifier regions in line and the subdecoder regions in line. A sense amplifier driver element is arranged in the subdecoder region and used in a sense amplifier operation.